

EXHIBIT H

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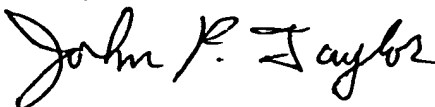
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Re: First Draft of Patent Application  
PROCESS FOR ETCHING A CONTROLLABLE  
THICKNESS OF OXIDE ON AN INTEGRATED  
CIRCUIT STRUCTURE ON A SEMICONDUCTOR  
SUBSTRATE USING NITROGEN PLASMA AND  
AN RF BIAS APPLIED TO THE SUBSTRATE  
LSI Docket No. 99-039

Gentlemen:

Enclosed is a first draft of your above captioned patent application for your review. Please note that there are questions, comments and blanks to be filled in. Ralph Veseli of the LSI Logic Intellectual Property Department has requested that this application be filed before the end of the year. I will be out of the office from November 13-30, returning to the office on December 1. Therefore, if you can complete your review of the enclosed draft and send me your comments by that date, we should be able to finish up the case and have it filed in the USPTO before the holidays.

Regards,



John P. Taylor  
Patent Attorney

Ralph R. Veseli, Patent Attorney LSI Logic Intellectual Property Department w/enclosure